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December 2013

FQP9N90C / FQPF9N90C

N-Channel QFET® MOSFET

900 V, 8.0 A, 1.4 Ω

Description

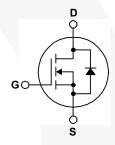
This N-Channel enhancement mode power MOSFET is • 8 A, 900 V, $R_{DS(on)}$ = 1.4 Ω (Max.) @ V_{GS} = 10 V, produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state

• Low Gate Charge (Typ. 45 nC) resistance, and to provide superior switching performance • Low Crss (Typ. 14 pF) and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power • 100% Avalanche Tested factor correction (PFC), and electronic lamp ballasts.

Features







Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter		FQP9N90C	FQPF9N90CT	Unit
V _{DSS}	Drain-Source Voltage		900		V
I _D	Drain Current - Continuous (T _C = 25°C)		8.0	8.0 *	Α
	- Continuous (T _C = 100°C)		2.8	2.8 *	Α
I _{DM}	Drain Current - Pulsed	(Note 1)	32	32 *	Α
V _{GSS}	Gate-Source Voltage		± 30		V
E _{AS}	Single Pulsed Avalanche Energy	(Note 2)	900		mJ
I _{AR}	Avalanche Current	(Note 1)	8.0		Α
E _{AR}	Repetitive Avalanche Energy	(Note 1)	20.5		mJ
dv/dt	Peak Diode Recovery dv/dt (r		4.0		V/ns
P_D	Power Dissipation (T _C = 25°C)		205	68	W
	- Derate above 25°C		1.64	0.54	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +150		°C
T _L	Maximum lead temperature for soldering, 1/8" from case for 5 seconds		300		°C

^{*} Drain current limited by maximum junction temperature

Thermal Characteristics

Symbol	Parameter	FQP9N90C	FQPF9N90CT	Unit	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.61	1.85	°C/W	
$R_{\theta JS}$	Thermal Resistance, Case-to-Sink Typ, Max.	0.5		°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	62.5	°C/W	

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQP9N90C	FQP9N90C	TO-220	Tube	N/A	N/A	50 units
FQPF9N90CT	FQPF9N90CT	TO-220F	Tube	N/A	N/A	50 units

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Cha	aracteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	900			V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C		0.99		V/°C
I _{DSS} Zero Gate \	Zoro Coto Voltago Droin Current	V _{DS} = 900 V, V _{GS} = 0 V			10	μΑ
	Zero Gate Voltage Drain Current	V _{DS} = 720 V, T _C = 125°C			10	μΑ
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 30 V, V _{DS} = 0 V			100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -30 V, V _{DS} = 0 V		-	-100	nA
On Cha	racteristics					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$	3.0		5.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 4 A		1.12	1.4	Ω
9 _{FS}	Forward Transconductance $V_{DS} = 40 \text{ V}, I_D = 4 \text{ A}$			9.2	-	S
C _{iss}	Input Capacitance	V _{DS} = 25 V, V _{GS} = 0 V,		2100	2730	pF
C _{oss}	Output Capacitance	f = 1.0 MHz		175	230	pF
C _{rss}	Reverse Transfer Capacitance			14	18	pF
Switchi	ing Characteristics					
t _{d(on)}	Turn-On Delay Time	V _{DD} = 450 V, I _D = 9.0A,		50	110	ns
t _r	Turn-On Rise Time	$R_G = 25 \Omega$		120	250	ns
t _{d(off)}	Turn-Off Delay Time	9		100	210	ns
t _f	Turn-Off Fall Time	(Note 4)		75	160	ns
Qg	Total Gate Charge	V _{DS} = 720 V, I _D = 9.0A,		45	58	nC
Q _{gs}	Gate-Source Charge	V _{GS} = 10 V	/	13		nC
Q _{gd}	Gate-Drain Charge	(Note 4)		18	-	nC
Drain-S	Source Diode Characteristics a	nd Maximum Ratings				
I _S	Maximum Continuous Drain-Source Diode Forward Current				8.0	Α
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current				32.0	Α
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 8 A			1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = 9 A,		550	/	ns
Q _{rr}	Reverse Recovery Charge	dI _F / dt = 100 A/μs		6.5		μС

Notes: 1. Repetitive rating : pulse-width limited by maximum junction temperature. 2. L = 21 mH, I_{AS} = 9 A, V_{DD} = 50 V, R_G = 25 Ω , starting T_J = 25°C. 3. $I_{SD} \le$ 9.0 A, di/dt \le 200 A/ μ s , $V_{DD} \le$ BV $_{DSS}$, starting T_J = 25°C. 4. Essentially independent of operating temperature.

Typical Characteristics

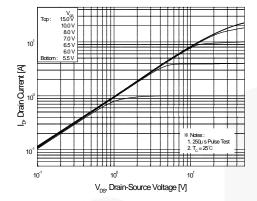


Figure 1. On-Region Characteristics

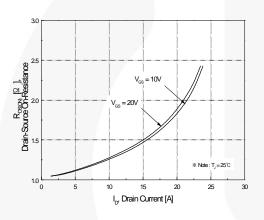


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

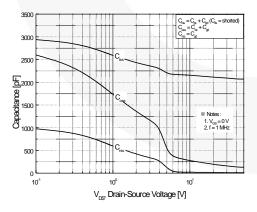


Figure 5. Capacitance Characteristics

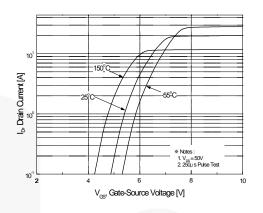


Figure 2. Transfer Characteristics

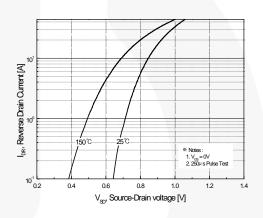


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

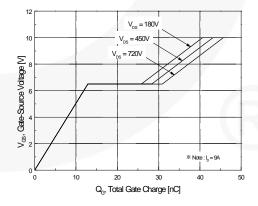


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

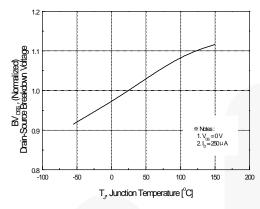


Figure 7. Breakdown Voltage Variation vs Temperature

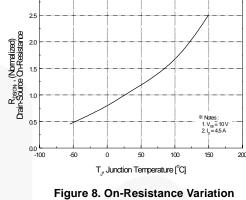


Figure 8. On-Resistance Variation vs Temperature

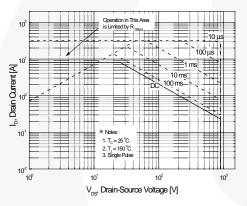


Figure 9-1. Maximum Safe Operating Area for FQP9N90C

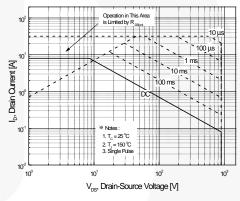


Figure 9-2. Maximum Safe Operating Area for FQPF9N90CT

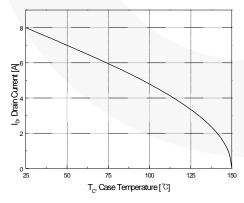


Figure 10. Maximum Drain Current vs Case Temperature

Typical Characteristics (Continued)

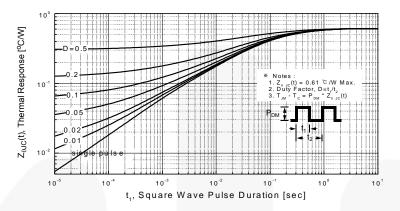


Figure 11-1. Transient Thermal Response Curve for FQP9N90C

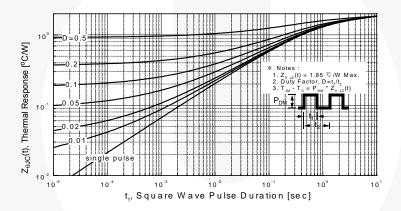


Figure 11-2. Transient Thermal Response Curve for FQPF9N90CT

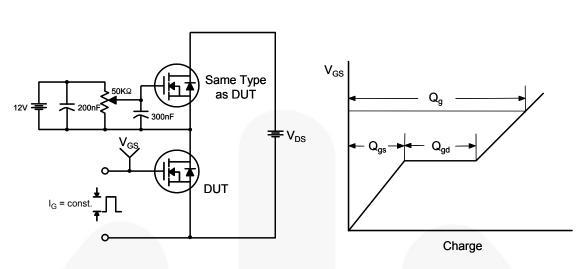


Figure 12. Gate Charge Test Circuit & Waveform

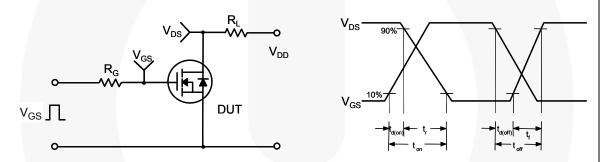


Figure 13. Resistive Switching Test Circuit & Waveforms

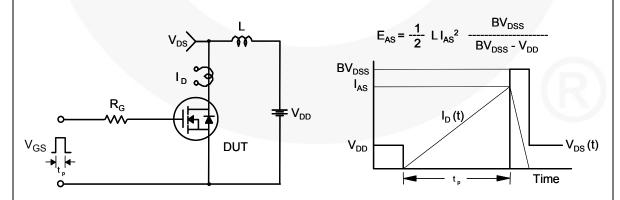
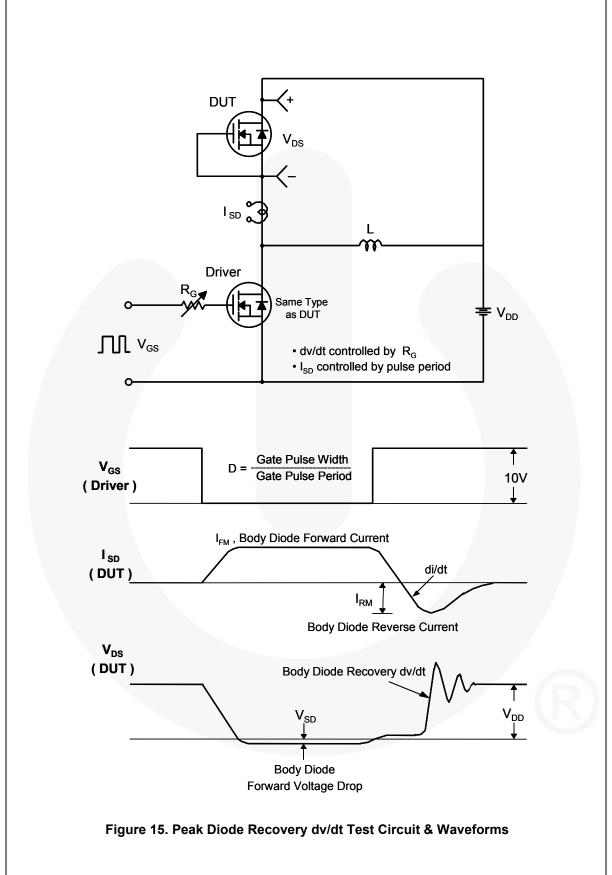


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



Mechanical Dimensions

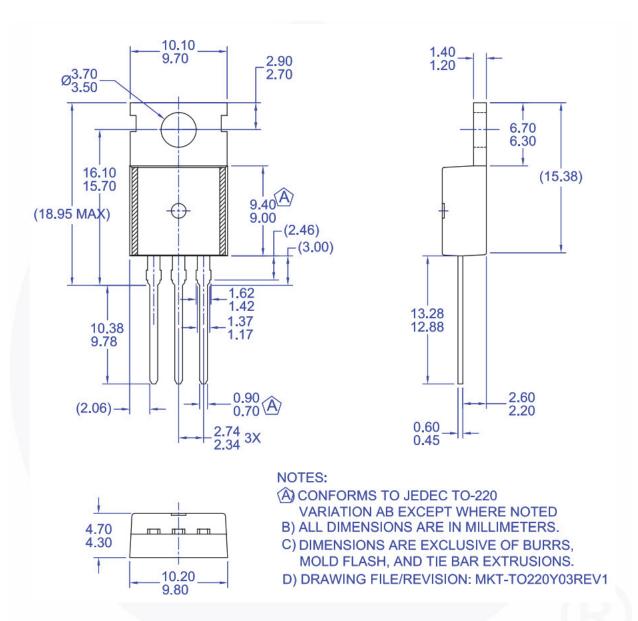


Figure 16. TO220, Molded, 3-Lead, Jedec Variation AB

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Mechanical Dimensions

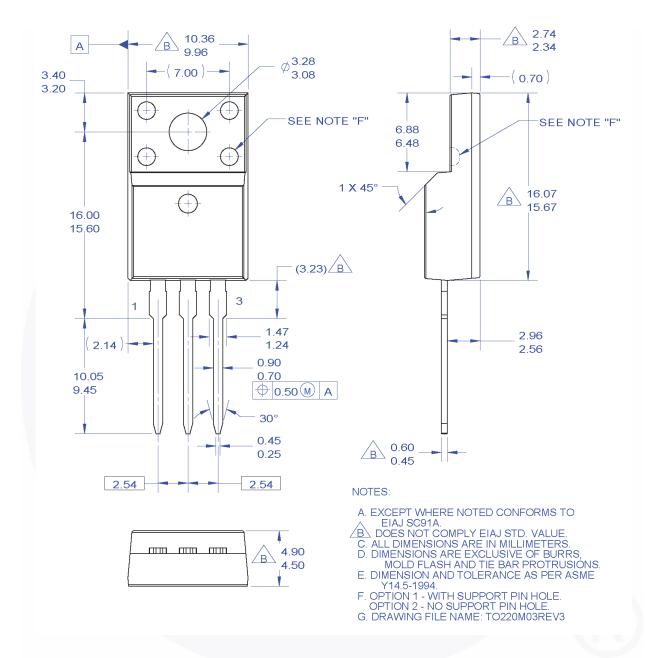


Figure 17. TO220, Molded, 3-Lead, Full Pack, EIAJ SC91, Straight Lead

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9

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